

REMARKS

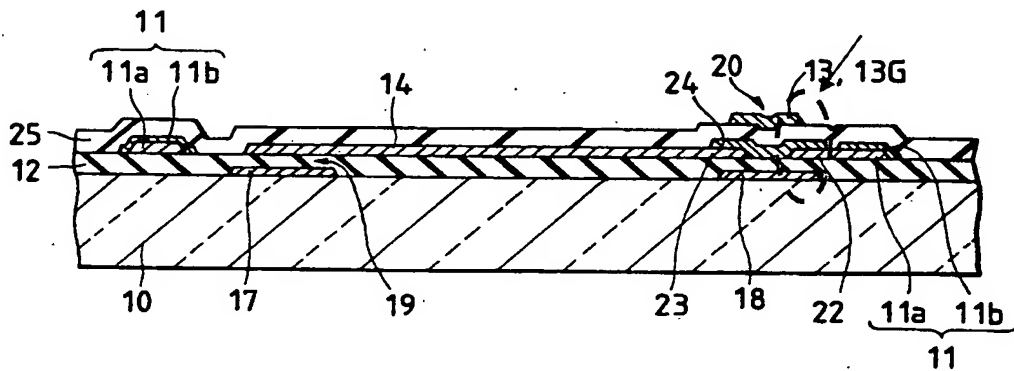
Claims 1-14 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Applicant's Related Art FIGs. 2 and 3F (hereinafter "APAF") in view of U.S. Patent No. 5,162,933 (hereinafter "Kakuda"). Applicant respectfully traverses the rejection as being based upon Applicant's Related Art and a reference that neither teaches nor suggests the novel combination of features recited by independent claim 1, and hence dependent claims 2-14.

With respect to independent claim 1, Applicant respectfully submits that neither of APAF nor Kakuda disclose a claimed combination comprising at least feature of "a plurality of thin film transistors formed on the substrate adjacent to intersections of the gate lines and the data lines, each thin film transistor including a gate electrode, a gate insulation layer, an active layer, an ohmic contact layer, a source electrode, and a drain electrode, the source electrode extended from each of the data lines and overlapping a portion of the gate electrode" and "wherein the source electrode is positioned between the ohmic contact layer and the metal layer."

The Office Action admits that Applicant's Related Art FIGs. 2 and 3F discloses all the features of claim 1, "except the metal layer formed on an entire surface of each of the data line and the source electrode." Accordingly, the Office Action relies upon Kakuda for allegedly showing "an LCD device having a data line 11 with a metal layer formed on the entire surface." In addition, the Office Action alleges that "a source electrode (22) extends from the data line (col. 4, lines 50-53) and is covered with a metal layer (11b in fig. 4). Applicant respectfully disagrees.

In figure 4 of Kakuda, a semiconductor layer (24) should be formed on a portion of the source electrode (22). The semiconductor layer (24) should bridge across a gap between the source and drain electrodes 22 and 23 (col. 4, lines 53-55). Accordingly, it is impossible for the metal layer (11b) to be formed on an entire surface of the source electrode (22).

Seeing below figure 4 of Kakuda, a portion of the semiconductor layer (24) is disposed directly on one portion of the source electrode (22). The metal layer (11b) may be formed on the other portion of the source electrode (22), while the semiconductor layer (24) is formed on one portion of the source electrode (22). Accordingly, Kakuda merely discloses a metal layer (11b) formed on a portion of the source electrode (22), not an entire surface of the source electrode (22).



For at least the above reasons, Applicants respectfully submit that claims 1-14 are neither taught nor suggested by APAF and/or Kakuda, whether taken alone or in combination. Thus, Applicant respectfully asserts that the rejections under 35 U.S.C. § 103(a) should be withdrawn because the above-discussed novel combination of features are neither taught nor suggested by any of the applied references.

CONCLUSION

In view of the foregoing, Applicants respectfully request reconsideration and the timely allowance of the pending claims. Should the Examiner feel that there are any issues outstanding after consideration of the Response, the Examiner is invited to contact the Applicants' undersigned representative to expedite prosecution.

EXCEPT for issue fees payable under 37 C.F.R. § 1.18, the Commissioner is hereby authorized by this paper to charge any additional fees during the entire pendency of this application including fees due under 37 C.F.R. §§ 1.16 and 1.17 which may be required, including any required extension of time fees, or credit any overpayment to Deposit Account No. 50-0310. This paragraph is intended to be a **CONSTRUCTIVE PETITION FOR EXTENSION OF TIME** in accordance with 37 C.F.R. § 1.136(a)(3).

Respectfully submitted,

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